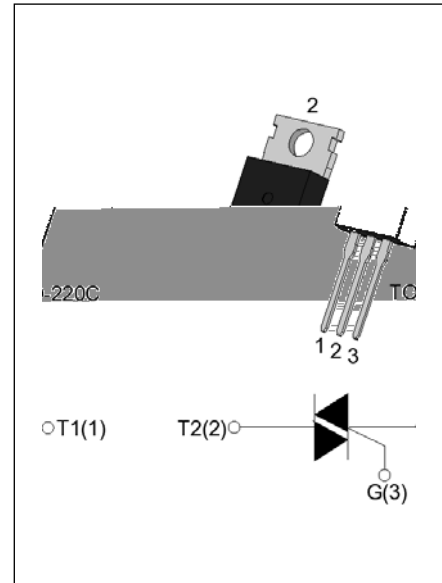


The JST138C-800D triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / / /$	5/5/5/10	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 98^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	95	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		105	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	45	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	50	$\text{A}/\mu\text{s}$
	-	20	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	3.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3KΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	15	mA
				20	
I _H	I _T =500mA		MAX.	10	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	40	V/μs
(dV/dt) _c	(dI/dt) _c =5A/ms, T _j =110		MIN.	2	V/μs
t _{on}	I _G =20mA I _A =200mA I _R =20mA T _j =25		TYP.	3	μs
t _{off}				30	

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =15A t _p =380μs	T _j =25	1.6	V
V _{TO}	Threshold voltage	T _j =125	0.8	V
R _D	Dynamic resistance	T _j =125	41	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25	5	μA
I _{RDM}		T _j =125	0.4	mA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	1.5	/W
R _{th(j-a)}	junction to ambient (AC)	60	/W

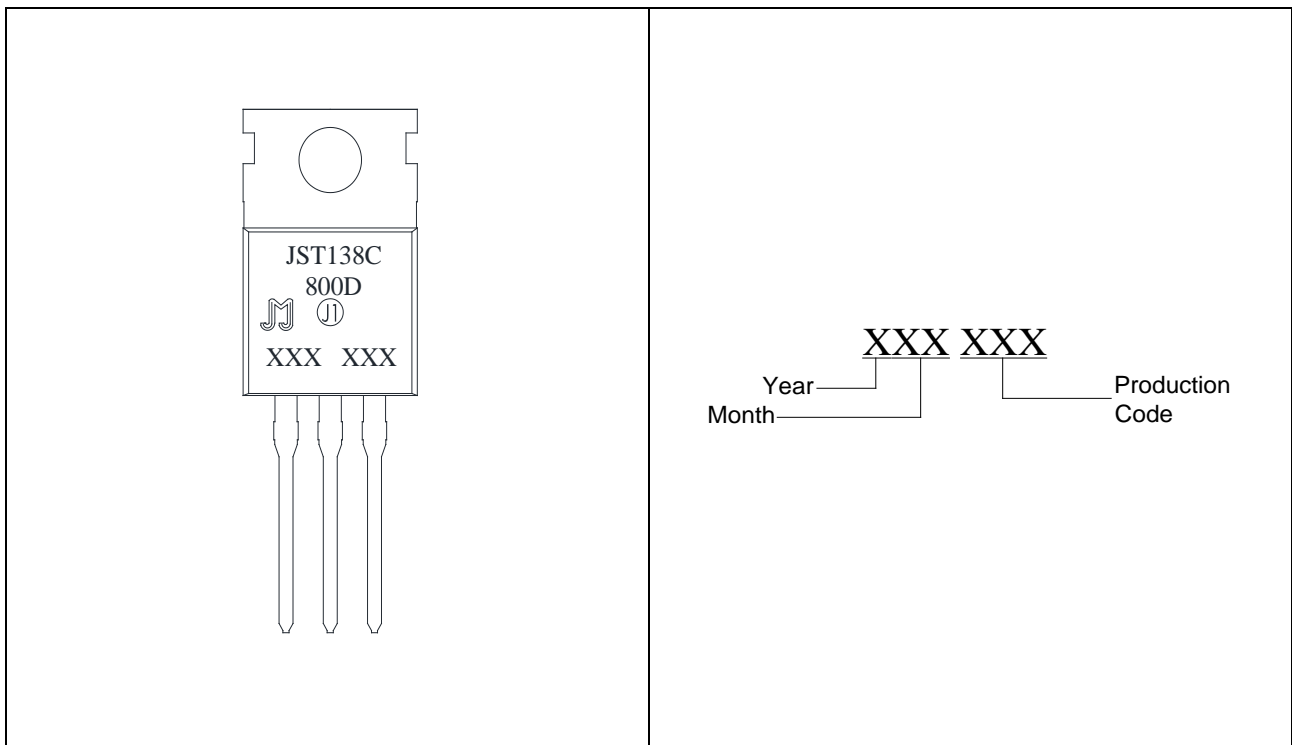
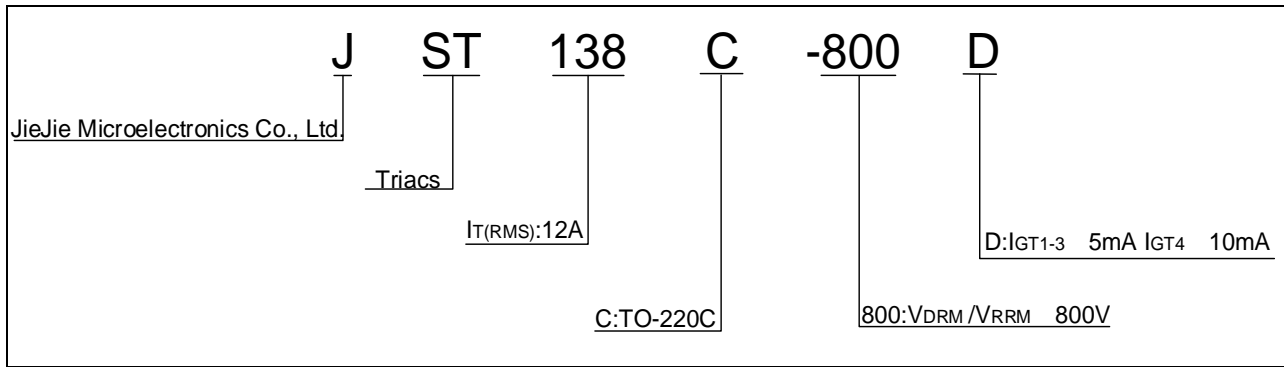


FIG.1 Maximum power dissipation versus RMS on-state current

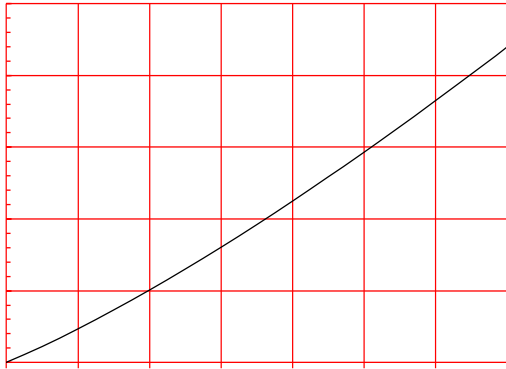
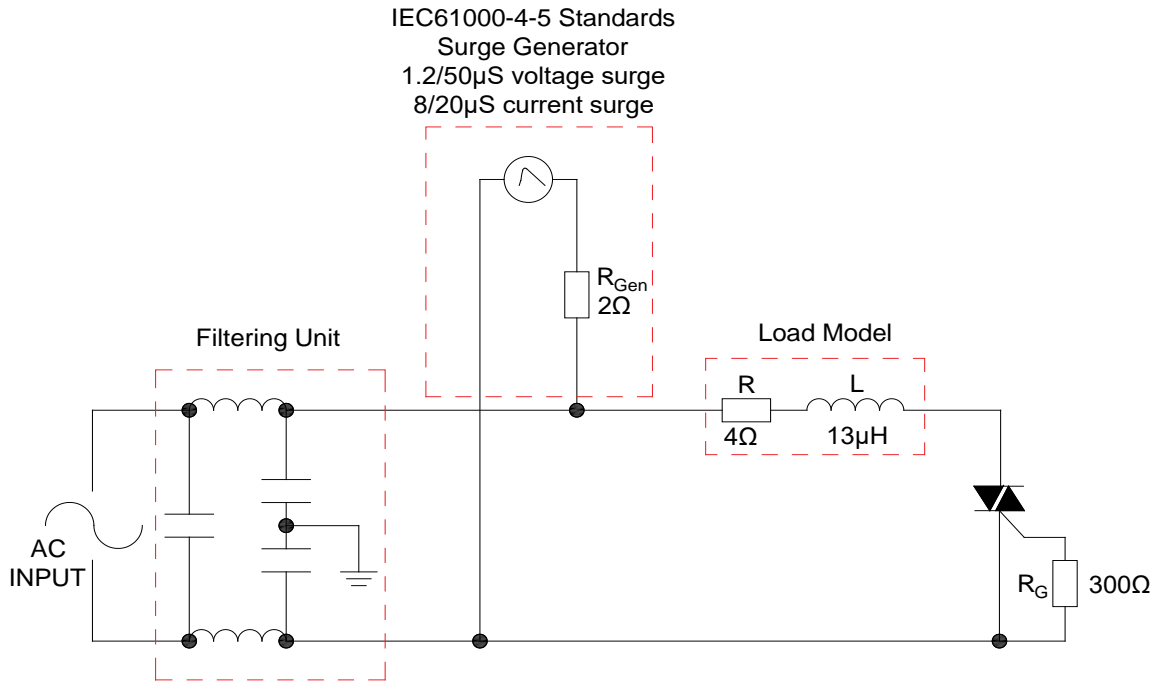


FIG.2: RMS on-state current versus case temperature

FIG.3: Surge peak on-state current versus number of cycles

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

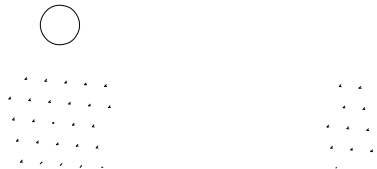


Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie.

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		-	-			
JST138C-800D	800	5	10	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.